





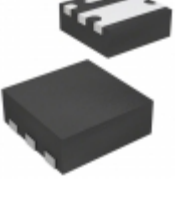
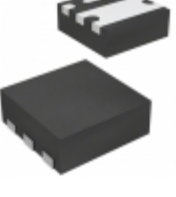

	<h2>SIA415DJ-T1-GE3</h2>
	<p>Hersteller-Teilenummer: SIA415DJ-T1-GE3</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET P-CH 20V 12A SC70-6</p> <p>Datenblätter:  SIA415DJ-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 3086 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SIA415DJ-T1-GE3
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 20V 12A SC70-6
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	3086 pcs Stock
detaillierte Beschreibung	P-Channel 20V 12A (Tc) 3.5W (Ta), 19W (Tc) Surface
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SC-70-6
Supplier Device-Gehäuse	PowerPAK® SC-70-6 Single
Verlustleistung (max)	3.5W (Ta), 19W (Tc)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	20V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	12A (Tc)
Rds On (Max) @ Id, Vgs	35 mOhm @ 5.6A, 4.5V
VGS (th) (Max) @ Id	1.5V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	47nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1250pF @ 10V
Antriebsspannung (Max Rds On, Min Rds On)	2.5V, 4.5V
Vgs (Max)	±12V
Verpackung	Tape & Reel (TR)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SIA415DJ-T1-GE3TR

SIA415DJ-T1-GE3 ist neu im Original, Suche SIA415DJ-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SIA415DJ-T1-GE3 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SIA415DJ-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SIA417DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 8V 12A SC70-6</p>	 <p>SIA415DJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 20V 12A SC70-6</p>	 <p>SIA414DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 8V 12A SC70-6</p>	 <p>SIA414DJ-TI-E3 Vishay Precision Group SIA414DJ-TI-E3 VISHAY</p>
 <p>SIA413DJ-T4-GE3 VISHAY SIA413DJ-T4-GE3 VISHAY</p>	 <p>SIA413DJ-T1-GE3 Vishay / Siliconix MOSFET P-CH 12V 12A SC70-6</p>	 <p>SIA416DJ-T1-GE3 Vishay / Siliconix MOSFET N-CH 100V 11.3A SC70-6L</p>	 <p>SIA416DJ-T1-GE3 Electro-Films (EFI) / Vishay MOSFET N-CH 100V 11.3A SC70-6L</p>

heiße Teile

Mehr

⊛ SIA400EDJ-T1-GE3	↔ SIA400EDJ-T1-GE3	⇒ SIA402DJ-T1-E3	D SIA406DJ-T1-GE3	↔ SIA406DJ-T1-GE3
↳ SIA408DJ-T1-GE3	⊛ SIA408DJ-T1-GE3	D SIA411DJ-T1-GE3	⇒ SIA411DJ-T1-GE3	↔ SIA413DJ-T1-GE3
⊛ SIA413DJ-T1-GE3	↳ SIA413DJ-T4-GE3	⊛ SIA414DJ-T1-GE3	↔ SIA414DJ-T1-GE3	↔ SIA415DJ-T1-GE3
D SIA417DJ-T1-GE3	⊛ SIA417DJ-T1-GE3	↳ SIA419DJ	⊛ SIA419DJ-T1-GE3	↔ SIA419DJ-T1-GE3
⇒ SIA421DJ-T1-GE3	↔ SIA421DJ-T1-GE3	⊛ SIA425EDJ-T1-GE3	↳ SIA425EDJ-T1-GE3	↔ SIA426DJ-T1-GE3
↔ SIA426DJ-T1-GE3	⇒ SIA427DJ-T1-GE3	D SIA427DJ-T1-GE3	⊛ SIA429DJ-T1-GE3	↳ SIA429DJ-T1-GE3
⊛ SIA430DJ-T1-GE3	D SIA430DJ-T1-GE3	⇒ SIA431DJ	↔ SIA431DJ-T1	↔ SIA431DJ-T1-GE3
↳ SIA431DJ-T1-GE3	⊛ SIA432DJ-T1-GE3	↔ SIA432DJ-T1-GE3	⇒ SIA433EDJ	↔ SIA433EDJ-T1-GE3
⊛ SIA433EDJ-T1-GE3	↳ SIA436DJ-T1-GE3	⊛ SIA436DJ-T1-GE3	D SIA443DJ-T1-GE3	↔ SIA443DJ-T1-GE3
↔ SIA444DJ-T1-GE3	⊛ SIA444DJ-T1-GE3	↳ SIA445EDJ-T1-GE3	⊛ SIA445EDJ-T1-GE3	↔ SIA447DJ-T1-GE3

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

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